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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	154
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1a3p600l-pqg208i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

# 2 – Flash\*Freeze Technology and Low Power Modes

## Flash\*Freeze Technology and Low Power Modes

Microsemi IGLOO,<sup>®</sup> IGLOO nano, IGLOO PLUS, ProASIC<sup>®</sup>3L, and Radiation-Tolerant (RT) ProASIC3 FPGAs with Flash\*Freeze technology are designed to meet the most demanding power and area challenges of today's portable electronics products with a reprogrammable, small-footprint, full-featured flash FPGA. These devices offer lower power consumption in static and dynamic modes, utilizing the unique Flash\*Freeze technology, than any other FPGA or CPLD.

IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 devices offer various power-saving modes that enable every system to utilize modes that achieve the lowest total system power. Low Power Active capability (static idle) allows for ultra-low power consumption while the device is operational in the system by maintaining SRAM, registers, I/Os, and logic functions.

Flash\*Freeze technology provides an ultra-low power static mode (Flash\*Freeze mode) that retains all SRAM and register information with rapid recovery to Active (operating) mode. IGLOO nano and IGLOO PLUS devices have an additional feature when operating in Flash\*Freeze mode, allowing them to retain I/O states as well as SRAM and register states. This mechanism enables the user to quickly (within 1  $\mu$ s) enter and exit Flash\*Freeze mode by activating the Flash\*Freeze (FF) pin while all power supplies are kept in their original states. In addition, I/Os and clocks connected to the FPGA can still be toggled without impact on device power consumption. While in Flash\*Freeze mode, the device retains all core register states and SRAM information. This mode can be configured so that no power is consumed by the I/O banks, clocks, JTAG pins, or PLLs; and the IGLOO and IGLOO PLUS devices consume as little as 5  $\mu$ W, while IGLOO nano devices consume as little as 2  $\mu$ W. Microsemi offers a state management IP core to aid users in gating clocks and managing data before entering Flash\*Freeze mode.

This document will guide users in selecting the best low power mode for their applications, and introduces Microsemi's Flash\*Freeze management IP core.

## **Spine Architecture**

The low power flash device architecture allows the VersaNet global networks to be segmented. Each of these networks contains spines (the vertical branches of the global network tree) and ribs that can reach all the VersaTiles inside its region. The nine spines available in a vertical column reside in global networks with two separate regions of scope: the quadrant global network, which has three spines, and the chip (main) global network, which has six spines. Note that the number of quadrant globals and globals/spines per tree varies depending on the specific device. Refer to Table 3-4 for the clocking resources available for each device. The spines are the vertical branches of the global network tree, shown in Figure 3-3 on page 50. Each spine in a vertical column of a chip (main) global network is further divided into two spine segments of equal lengths: one in the top and one in the bottom half of the die (except in 10 k through 30 k gate devices).

Top and bottom spine segments radiating from the center of a device have the same height. However, just as in the ProASIC<sup>PLUS®</sup> family, signals assigned only to the top and bottom spine cannot access the middle two rows of the die. The spines for quadrant clock networks do not cross the middle of the die and cannot access the middle two rows of the architecture.

Each spine and its associated ribs cover a certain area of the device (the "scope" of the spine; see Figure 3-3 on page 50). Each spine is accessed by the dedicated global network MUX tree architecture, which defines how a particular spine is driven—either by the signal on the global network from a CCC, for example, or by another net defined by the user. Details of the chip (main) global network spine-selection MUX are presented in Figure 3-8 on page 60. The spine drivers for each spine are located in the middle of the die.

Quadrant spines can be driven from user I/Os or an internal signal from the north and south sides of the die. The ability to drive spines in the quadrant global networks can have a significant effect on system performance for high-fanout inputs to a design. Access to the top quadrant spine regions is from the top of the die, and access to the bottom quadrant spine regions is from the bottom of the die. The A3PE3000 device has 28 clock trees and each tree has nine spines; this flexible global network architecture enables users to map up to 252 different internal/external clocks in an A3PE3000 device.

			Orrections		Globals/	Total			Rows
ProASIC3/ ProASIC3L Devices	IGLOO Devices	Chip Globals	Globals (4×3)	Clock Trees	per Tree	per Device	in Each Tree	Total VersaTiles	Each Spine
A3PN010	AGLN010	4	0	1	0	0	260	260	4
A3PN015	AGLN015	4	0	1	0	0	384	384	6
A3PN020	AGLN020	4	0	1	0	0	520	520	6
A3PN060	AGLN060	6	12	4	9	36	384	1,536	12
A3PN125	AGLN125	6	12	8	9	72	384	3,072	12
A3PN250	AGLN250	6	12	8	9	72	768	6,144	24
A3P015	AGL015	6	0	1	9	9	384	384	12
A3P030	AGL030	6	0	2	9	18	384	768	12
A3P060	AGL060	6	12	4	9	36	384	1,536	12
A3P125	AGL125	6	12	8	9	72	384	3,072	12
A3P250/L	AGL250	6	12	8	9	72	768	6,144	24
A3P400	AGL400	6	12	12	9	108	768	9,216	24
A3P600/L	AGL600	6	12	12	9	108	1,152	13,824	36
A3P1000/L	AGL1000	6	12	16	9	144	1,536	24,576	48
A3PE600/L	AGLE600	6	12	12	9	108	1,120	13,440	35
A3PE1500		6	12	20	9	180	1,888	37,760	59
A3PE3000/L	AGLE3000	6	12	28	9	252	2,656	74,368	83

Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices



Global Resources in Low Power Flash Devices

The following will happen during demotion of a global signal to regular nets:

- CLKBUF\_x becomes INBUF\_x; CLKINT is removed from the netlist.
- The essential global macro, such as the output of the Clock Conditioning Circuit, cannot be demoted.
- No automatic buffering will happen.

Since no automatic buffering happens when a signal is demoted, this net may have a high delay due to large fanout. This may have a negative effect on the quality of the results. Microsemi recommends that the automatic global demotion only be used on small-fanout nets. Use clock networks for high-fanout nets to improve timing and routability.

#### **Spine Assignment**

The low power flash device architecture allows the global networks to be segmented and used as clock spines. These spines, also called local clock networks, enable the use of PDC or MVN to assign a signal to a spine.

PDC syntax to promote a net to a spine/local clock:

assign\_local\_clock -net netname -type [quadrant|chip] Tn|Bn|Tn:Bm

If the net is driven by a clock macro, Designer automatically demotes the clock net to a regular net before it is assigned to a spine. Nets driven by a PLL or CLKDLY macro cannot be assigned to a local clock.

When assigning a signal to a spine or quadrant global network using PDC (pre-compile), the Designer software will legalize the shared instances. The number of shared instances to be legalized can be controlled by compile options. If these networks are created in MVN (only quadrant globals can be created), no legalization is done (as it is post-compile). Designer does not do legalization between non-clock nets.

As an example, consider two nets, net\_clk and net\_reset, driving the same flip-flop. The following PDC constraints are used:

#### assign\_local\_clock -net net\_clk -type chip T3

assign\_local\_clock -net net\_reset -type chip T1:T2

During Compile, Designer adds a buffer in the reset net and places it in the T1 or T2 region, and places the flip-flop in the T3 spine region (Figure 3-16).



assign\_local\_clock -net net\_clk -type chip T3 assign\_local\_clock -net net\_reset -type chip T1:T2

Figure 3-16 • Adding a Buffer for Shared Instances

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Figure 4-22 • CCC Block Control Bits – Graphical Representation of Assignments

Use quadrant global region assignments by finding the clock net associated with the CCC macro under the Nets tab and creating a quadrant global region for the net, as shown in Figure 4-33.

#### Figure 4-33 • Quadrant Clock Assignment for a Global Net

#### External I/O–Driven CCCs

The above-mentioned recommendation for proper layout techniques will ensure the correct assignment. It is possible that, especially with External I/O–Driven CCC macros, placement of the CCC macro in a desired location may not be achieved. For example, assigning an input port of an External I/O–Driven CCC near a particular CCC location does not guarantee global assignments to the desired location. This is because the clock inputs of External I/O–Driven CCCs can be assigned to any I/O location; therefore, it is possible that the CCC connected to the clock input will be routed to a location other than the one closest to the I/O location, depending on resource availability and placement constraints.

#### **Clock Placer**

The clock placer is a placement engine for low power flash devices that places global signals on the chip global and quadrant global networks. Based on the clock assignment constraints for the chip global and quadrant global clocks, it will try to satisfy all constraints, as well as creating quadrant clock regions when necessary. If the clock placer fails to create the quadrant clock regions for the global signals, it will report an error and stop Layout.

The user must ensure that the constraints set to promote clock signals to quadrant global networks are valid.

## **Cascading CCCs**

The CCCs in low power flash devices can be cascaded. Cascading CCCs can help achieve more accurate PLL output frequency results than those achievable with a single CCC. In addition, this technique is useful when the user application requires the output clock of the PLL to be a multiple of the reference clock by an integer greater than the maximum feedback divider value of the PLL (divide by 128) to achieve the desired frequency.

For example, the user application may require a 280 MHz output clock using a 2 MHz input reference clock, as shown in Figure 4-34 on page 126.

## FlashROM Generation and Instantiation in the Design

The SmartGen core generator, available in Libero SoC and Designer, is the only tool that can be used to generate the FlashROM content. SmartGen has several user-friendly features to help generate the FlashROM contents. Instead of selecting each byte and assigning values, you can create a region within a page, modify the region, and assign properties to that region. The FlashROM user interface, shown in Figure 5-10, includes the configuration grid, existing regions list, and properties field. The properties field specifies the region-specific information and defines the data used for that region. You can assign values to the following properties:

- Static Fixed Data—Enables you to fix the data so it cannot be changed during programming time. This option is useful when you have fixed data stored in this region, which is required for the operation of the design in the FPGA. Key storage is one example.
- Static Modifiable Data—Select this option when the data in a particular region is expected to be static data (such as a version number, which remains the same for a long duration but could conceivably change in the future). This option enables you to avoid changing the value every time you enter new data.
- 3. Read from File—This provides the full flexibility of FlashROM usage to the customer. If you have a customized algorithm for generating the FlashROM data, you can specify this setting. You can then generate a text file with data for as many devices as you wish to program, and load that into the FlashPoint programming file generation software to get programming files that include all the data. SmartGen will optionally pass the location of the file where the data is stored if the file is specified in SmartGen. Each text file has only one type of data format (binary, decimal, hex, or ASCII text). The length of each data file must be shorter than or equal to the selected region length. If the data is shorter than the selected region length, the most significant bits will be padded with 0s. For multiple text files for multiple regions, the first lines are for the first device. In SmartGen, Load Sim. Value From File allows you to load the first device data in the MEM file for simulation.
- 4. Auto Increment/Decrement—This scenario is useful when you specify the contents of FlashROM for a large number of devices in a series. You can specify the step value for the serial number and a maximum value for inventory control. During programming file generation, the actual number of devices to be programmed is specified and a start value is fed to the software.

Figure 5-10 • SmartGen GUI of the FlashROM

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices



Notes:

2. Flash\*Freeze is supported in all IGLOO devices and the ProASIC3L devices.

Figure 6-1 • IGLOO and ProASIC3 Device Architecture Overview

<sup>1.</sup> AES decryption not supported in 30 k gate devices and smaller.

#### Table 6-10 • RAM and FIFO Memory Block Consumption

		Depth										
			2	56	512	1,024	2,048	4,096	8,192	16,384	32,768	65,536
			Two-Port	Dual-Port	Dual-Port	Dual-Port	Dual-Port	Dual-Port	Dual-Port	Dual-Port	Dual-Port	Dual-Port
	1	Number Block	1	1	1	1	1	1	2	4	8	16 × 1
		Configuration	Any	Any	Any	1,024 × 4	2,048 × 2	4,096 × 1	2 × (4,096 × 1) Cascade Deep	4 × (4,096 × 1) Cascade Deep	8 × (4,096 × 1) Cascade Deep	16 × (4,096 × 1) Cascade Deep
	2	Number Block	1	1	1	1	1	2	4	8	16	32
		Configuration	Any	Any	Any	1,024×4	2,048 × 2	2 × (4,096 × 1) Cascaded Wide	4 × (4,096 × 1) Cascaded 2 Deep and 2 Wide	8 × (4,096 × 1) Cascaded 4 Deep and 2 Wide	16 × (4,096 × 1) Cascaded 8 Deep and 2 Wide	32 × (4,096 × 1) Cascaded 16 Deep and 2 Wide
	4	Number Block	1	1	1	1	2	4	8	16	32	64
		Configuration	Any	Any	Any	1,024 × 4	2 × (2,048 × 2) Cascaded Wide	4 × (4,096 × 1) Cascaded Wide	4 × (4,096 × 1) Cascaded 2 Deep and 4 Wide	16 × (4,096 × 1) Cascaded 4 Deep and 4 Wide	32 × (4,096 × 1) Cascaded 8 Deep and 4 Wide	64 × (4,096 × 1) Cascaded 16 Deep and 4 Wide
	8	Number Block	1	1	1	2	4	8	16	32	64	
		Configuration	Any	Any	Any	2 × (1,024 × 4) Cascaded Wide	4 × (2,048 × 2) Cascaded Wide	8 × (4,096 × 1) Cascaded Wide	16 × (4,096 × 1) Cascaded 2 Deep and 8 Wide	32 × (4,096 × 1) Cascaded 4 Deep and 8 Wide	64 × (4,096 × 1) Cascaded 8 Deep and 8 Wide	
	9	Number Block	1	1	1	2	4	8	16	32		
		Configuration	Any	Any	Any	2 × (512 × 9) Cascaded Deep	4 × (512 × 9) Cascaded Deep	8 × (512 × 9) Cascaded Deep	16 × (512 × 9) Cascaded Deep	32 × (512 × 9) Cascaded Deep		
	16	Number Block	1	1	1	4	8	16	32	64		
Width		Configuration	256 × 18	256 × 18	256 × 18	4 × (1,024 × 4) Cascaded Wide	8 × (2,048 × 2) Cascaded Wide	16 × (4,096 × 1) Cascaded Wide	32 × (4,096 × 1) Cascaded 2 Deep and 16 Wide	32 × (4,096 × 1) Cascaded 4 Deep and 16 Wide		
	18	Number Block	1	2	2	4	8	18	32			
		Configuration	256 × 8	2 × (512 × 9) Cascaded Wide	2 × (512 × 9) Cascaded Wide	4 × (512 × 9) Cascaded 2 Deep and 2 Wide	8 × (512 × 9) Cascaded 4 Deep and 2 Wide	16 × (512 × 9) Cascaded 8 Deep and 2 Wide	16 × (512 × 9) Cascaded 16 Deep and 2 Wide			
	32	Number Block	2	4	4	8	16	32	64			
		Configuration	2 × (256 × 18) Cascaded Wide	4 × (512 × 9) Cascaded Wide	4 × (512 × 9) Cascaded Wide	8 × (1,024 × 4) Cascaded Wide	16 × (2,048 × 2) Cascaded Wide	32 × (4,096 × 1) Cascaded Wide	64 × (4,096 × 1) Cascaded 2 Deep and 32 Wide			
	36	Number Block	2	4	4	8	16	32				
		Configuration	2 × (256 × 18) Cascaded Wide	4 × (512 × 9) Cascaded Wide	4 × (512 × 9) Cascaded Wide	4 × (512 × 9) Cascaded 2 Deep and 4 Wide	16 × (512 × 9) Cascaded 4 Deep and 4 Wide	16 × (512 × 9) Cascaded 8 Deep and 4 Wide				
	64	Number Block	4	8	8	16	32	64				
		Configuration	4 × (256 × 18) Cascaded Wide	8 × (512 × 9) Cascaded Wide	8 × (512 × 9) Cascaded Wide	16 × (1,024 × 4) Cascaded Wide	32 × (2,048 × 2) Cascaded Wide	64 × (4,096 × 1) Cascaded Wide				
	72	Number Block	4	8	8	16	32					
		Configuration	4 × (256 × 18) Cascaded Wide	8 × (512 × 9) Cascaded Wide	8 × (512 × 9) Cascaded Wide	16 × (512 × 9) Cascaded Wide	16 × (512 × 9) Cascaded 4 Deep and 8 Wide					

Note: Memory configurations represented by grayed cells are not supported.

# Conclusion

Fusion, IGLOO, and ProASIC3 devices provide users with extremely flexible SRAM blocks for most design needs, with the ability to choose between an easy-to-use dual-port memory or a wide-word two-port memory. Used with the built-in FIFO controllers, these memory blocks also serve as highly efficient FIFOs that do not consume user gates when implemented. The SmartGen core generator provides a fast and easy way to configure these memory elements for use in designs.

# **List of Changes**

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes F							
August 2012	The note connected with Figure 6-3 • Supported Basic RAM Macros, regarding RAM4K9, was revised to explain that it applies only to part numbers of certain revisions and earlier (SAR 29574).	152						
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A						
v1.5 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 6-1 • Flash-Based FPGAs.	150						
	IGLOO nano and ProASIC3 nano devices were added to Figure 6-8 • Interfacing TAP Ports and SRAM Blocks.	164						
v1.4 (October 2008)	The "SRAM/FIFO Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	150						
	The "SRAM and FIFO Architecture" section was modified to remove "IGLOO and ProASIC3E" from the description of what the memory block includes, as this statement applies to all memory blocks.							
	Wording in the "Clocking" section was revised to change "IGLOO and ProASIC3 devices support inversion" to "Low power flash devices support inversion." The reference to IGLOO and ProASIC3 development tools in the last paragraph of the section was changed to refer to development tools in general.	157						
	The "ESTOP and FSTOP Usage" section was updated to refer to FIFO counters in devices in general rather than only IGLOO and ProASIC3E devices.	160						
v1.3 (August 2008)	The note was removed from Figure 6-7 • RAM Block with Embedded FIFO Controller and placed in the WCLK and RCLK description.	158						
	The "WCLK and RCLK" description was revised.	159						
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 6-1 • Flash- Based FPGAs:	150						
	ProASIC3L was updated to include 1.5 V.							
	The number of PLLs for ProASIC3E was changed from five to six.							
v1.1 (March 2008)	The "Introduction" section was updated to include the IGLOO PLUS family.	147						
	The "Device Architecture" section was updated to state that 15 k gate devices do not support SRAM and FIFO.	147						
	The first note in Figure 6-1 • IGLOO and ProASIC3 Device Architecture Overview was updated to include mention of 15 k gate devices, and IGLOO PLUS was added to the second note.	149						

# Advanced I/Os—IGLOO, ProASIC3L, and ProASIC3

Table 7-2 and Table 7-3 show the voltages and compatible I/O standards for the IGLOO, ProASIC3L, and ProASIC3 families.

I/Os provide programmable slew rates (except 30 K gate devices), drive strengths, and weak pull-up and pull-down circuits. 3.3 V PCI and 3.3 V PCI-X can be configured to be 5 V–tolerant. See the "5 V Input Tolerance" section on page 194 for possible implementations of 5 V tolerance.

All I/Os are in a known state during power-up, and any power-up sequence is allowed without current impact. Refer to the "I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)" section in the datasheet for more information. During power-up, before reaching activation levels, the I/O input and output buffers are disabled while the weak pull-up is enabled. Activation levels are described in the datasheet.

IGLOO	AGL015	AGL030	AGL060	AGL125	AGL250		AGL600	AGL1000	
ProASIC3	A3P015	A3P030	A3P060	A3P125	A3P250/ A3P250L	A3P400	A3P600/ A3P600L	A3P1000/ A3P1000L	
Single-Ended									
LVTTL/LVCMOS 3.3 V, LVCMOS 2.5 V / 1.8 V / 1.5 V / 1.2 V LVCMOS 2.5 V / 5.0 V	1	1	1	1	1	1	1	1	
3.3 V PCI/PCI-X	-	-	1	1	1	1	1	1	
Differential									
LVPECL, LVDS, B-LVDS, M-LVDS	_	_	_	_	1	1	1	1	

Table 7-2 • Supported I/O Standards

## I/O Banks and I/O Standards Compatibility

I/Os are grouped into I/O voltage banks.

Each I/O voltage bank has dedicated I/O supply and ground voltages (VMV/GNDQ for input buffers and VCCI/GND for output buffers). This isolation is necessary to minimize simultaneous switching noise from the input and output (SSI and SSO). The switching noise (ground bounce and power bounce) is generated by the output buffers and transferred into input buffer circuits, and vice versa. Because of these dedicated supplies, only I/Os with compatible standards can be assigned to the same I/O voltage bank. Table 7-3 shows the required voltage compatibility values for each of these voltages.

There are four I/O banks on the 250K gate through 1M gate devices.

There are two I/O banks on the 30K, 60K, and 125K gate devices.

I/O standards are compatible if their VCCI and VMV values are identical. VMV and GNDQ are "quiet" input power supply pins and are not used on 30K gate devices (Table 7-3).

Table 7-3 • VCCI Voltages and Compatible IGLOO and ProASIC3 Standards

VCCI and VMV (typical)	Compatible Standards
3.3 V	LVTTL/LVCMOS 3.3, PCI 3.3, PCI-X 3.3 LVPECL
2.5 V	LVCMOS 2.5, LVCMOS 2.5/5.0, LVDS, B-LVDS, M-LVDS
1.8 V	LVCMOS 1.8
1.5 V	LVCMOS 1.5
1.2 V	LVCMOS 1.2

I/O Structures in IGLOO and ProASIC3 Devices

	Maximum Performance							
Specification	ProASIC3	IGLOO V2 or V5 Devices, 1.5 V DC Core Supply Voltage	IGLOO V2, 1.2 V DC Core Supply Voltage					
LVTTL/LVCMOS 3.3 V	200 MHz	180 MHz	TBD					
LVCMOS 2.5 V	250 MHz	230 MHz	TBD					
LVCMOS 1.8 V	200 MHz	180 MHz	TBD					
LVCMOS 1.5 V	130 MHz	120 MHz	TBD					
PCI	200 MHz	180 MHz	TBD					
PCI-X	200 MHz	180 MHz	TBD					
LVDS	350 MHz	300 MHz	TBD					
LVPECL	350 MHz	300 MHz	TBD					

# Table 7-6 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in IGLOO and ProASIC Devices (maximum drive strength and high slew selected)

# **User I/O Naming Convention**

## **IGLOO and ProASIC3**

Due to the comprehensive and flexible nature of IGLOO and ProASIC3 device user I/Os, a naming scheme is used to show the details of each I/O (Figure 7-19 on page 207 and Figure 7-20 on page 207). The name identifies to which I/O bank it belongs, as well as pairing and pin polarity for differential I/Os.

I/O Nomenclature = FF/Gmn/IOuxwBy

Gmn is only used for I/Os that also have CCC access—i.e., global pins.

- FF = Indicates the I/O dedicated for the Flash\*Freeze mode activation pin in IGLOO and ProASIC3L devices only
- G = Global
- m = Global pin location associated with each CCC on the device: A (northwest corner), B (northeast corner), C (east middle), D (southeast corner), E (southwest corner), and F (west middle)
- n = Global input MUX and pin number of the associated Global location m—either A0, A1, A2, B0, B1, B2, C0, C1, or C2. Refer to the "Global Resources in Low Power Flash Devices" section on page 47 for information about the three input pins per clock source MUX at CCC location m.
- u = I/O pair number in the bank, starting at 00 from the northwest I/O bank and proceeding in a clockwise direction
- x = P or U (Positive), N or V (Negative) for differential pairs, or R (Regular—single-ended) for the I/Os that support single-ended and voltage-referenced I/O standards only. U (Positive) or V (Negative)—for LVDS, DDR LVDS, B-LVDS, and M-LVDS only—restricts the I/O differential pair from being selected as an LVPECL pair.
- w = D (Differential Pair), P (Pair), or S (Single-Ended). D (Differential Pair) if both members of the pair are bonded out to adjacent pins or are separated only by one GND or NC pin; P (Pair) if both members of the pair are bonded out but do not meet the adjacency requirement; or S (Single-Ended) if the I/O pair is not bonded out. For Differential Pairs (D), adjacency for ball grid packages means only vertical or horizontal. Diagonal adjacency does not meet the requirements for a true differential pair.
- B = Bank
- y = Bank number (0–3). The Bank number starts at 0 from the northwest I/O bank and proceeds in a clockwise direction.

I/O Structures in IGLOO and ProASIC3 Devices

## **Board-Level Considerations**

Low power flash devices have robust I/O features that can help in reducing board-level components. The devices offer single-chip solutions, which makes the board layout simpler and more immune to signal integrity issues. Although, in many cases, these devices resolve board-level issues, special attention should always be given to overall signal integrity. This section covers important board-level considerations to facilitate optimum device performance.

#### Termination

Proper termination of all signals is essential for good signal quality. Nonterminated signals, especially clock signals, can cause malfunctioning of the device.

For general termination guidelines, refer to the *Board-Level Considerations* application note for Microsemi FPGAs. Also refer to the "Pin Descriptions" chapter of the appropriate datasheet for termination requirements for specific pins.

Low power flash I/Os are equipped with on-chip pull-up/-down resistors. The user can enable these resistors by instantiating them either in the top level of the design (refer to the *IGLOO, Fusion, and ProASIC3 Macro Library Guide* for the available I/O macros with pull-up/-down) or in the I/O Attribute Editor in Designer if generic input or output buffers are instantiated in the top level. Unused I/O pins are configured as inputs with pull-up resistors.

As mentioned earlier, low power flash devices have multiple programmable drive strengths, and the user can eliminate unwanted overshoot and undershoot by adjusting the drive strengths.

## **Power-Up Behavior**

Low power flash devices are power-up/-down friendly; i.e., no particular sequencing is required for power-up and power-down. This eliminates extra board components for power-up sequencing, such as a power-up sequencer.

During power-up, all I/Os are tristated, irrespective of I/O macro type (input buffers, output buffers, I/O buffers with weak pull-ups or weak pull-downs, etc.). Once I/Os become activated, they are set to the user-selected I/O macros. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details.

## **Drive Strength**

Low power flash devices have up to seven programmable output drive strengths. The user can select the drive strength of a particular output in the I/O Attribute Editor or can instantiate a specialized I/O macro, such as OUTBUF\_S\_12 (slew = low, out\_drive = 12 mA).

The maximum available drive strength is 24 mA per I/O. Though no I/O should be forced to source or sink more than 24 mA indefinitely, I/Os may handle a higher amount of current (refer to the device IBIS model for maximum source/sink current) during signal transition (AC current). Every device package has its own power dissipation limit; hence, power calculation must be performed accurately to determine how much current can be tolerated per I/O within that limit.

## I/O Interfacing

Low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected (refer to the "5 V Input and Output Tolerance" section on page 194). Along with other low-voltage I/O macros, this 5 V tolerance makes these devices suitable for many types of board component interfacing.

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Date	Change	Page
June 2011 (continued)	The following sentence was removed from the "LVCMOS (Low-Voltage CMOS)" section (SAR 22634): "All these versions use a 3.3 V-tolerant CMOS input buffer and a push-pull output buffer."	184
	Hot-insertion was changed to "No" for other IGLOO and all ProASIC3 devices in Table 7-12 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in IGLOO and ProASIC3 Devices (SAR 24526).	193
	The "Electrostatic Discharge Protection" section was revised to remove references to tolerances (refer to the <i>Reliability Report</i> for tolerances). The Machine Model (MM) is not supported and was deleted from this section (SAR 24385).	192
	The "I/O Interfacing" section was revised to state that low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected, removing "without adding any extra circuitry," which was incorrect (SAR 21404).	208
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.4 (December 2008)	The terminology in the "Low Power Flash Device I/O Support" section was revised.	176
v1.3 (October 2008)	The "Low Power Flash Device I/O Support" section was revised to include new families and make the information more concise.	176
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 7-1 • Flash-Based FPGAs:	176
	<ul> <li>ProASIC3L was updated to include 1.5 V.</li> </ul>	
	<ul> <li>The number of PLLs for ProASIC3E was changed from five to six.</li> </ul>	
v1.1 (March 2008)	Originally, this document contained information on all IGLOO and ProASIC3 families. With the addition of new families and to highlight the differences between the features, the document has been separated into 3 documents:	N/A
	This document contains information specific to IGLOO, ProASIC3, and ProASIC3L.	
	"I/O Structures in IGLOOe and ProASIC3E Devices" in the <i>ProASIC3E FPGA Fabric User's Guide</i> contains information specific to IGLOOe, ProASIC3E, and ProASIC3EL I/O features.	
	"I/O Structures in IGLOO PLUS Devices" in the IGLOO PLUS FPGA Fabric User's Guide contains information specific to IGLOO PLUS I/O features.	

I/O Structures in IGLOOe and ProASIC3E Devices

IGLOOe and ProASIC3E devices support output slew rate control: high and low. Microsemi recommends the high slew rate option to minimize the propagation delay. This high-speed option may introduce noise into the system if appropriate signal integrity measures are not adopted. Selecting a low slew rate reduces this kind of noise but adds some delays in the system. Low slew rate is recommended when bus transients are expected.

#### **Output Drive**

The output buffers of IGLOOe and ProASIC3E devices can provide multiple drive strengths to meet signal integrity requirements. The LVTTL and LVCMOS (except 1.2 V LVCMOS) standards have selectable drive strengths. Other standards have a preset value.

Drive strength should also be selected according to the design requirements and noise immunity of the system.

The output slew rate and multiple drive strength controls are available in LVTTL/LVCMOS 3.3 V, LVCMOS 2.5 V, LVCMOS 2.5 V / 5.0 V input, LVCMOS 1.8 V, and LVCMOS 1.5 V. All other I/O standards have a high output slew rate by default.

For other IGLOOe and ProASIC3E devices, refer to Table 8-15 for more information about the slew rate and drive strength specification.

There will be a difference in timing between the Standard Plus I/O banks and the Advanced I/O banks. Refer to the I/O timing tables in the datasheet for the standards supported by each device.

I/O Standards	2 mA	4 mA	6 mA	8 mA	12 mA	16 mA	24 mA	Slew	
LVTTL/LVCMOS 3.3 V	1	1	1	~	~	1	~	High	Low
LVCMOS 2.5 V	~	1	1	1	~	1	~	High	Low
LVCMOS 2.5/5.0 V	1	1	1	~	~	1	~	High	Low
LVCMOS 1.8 V	1	1	1	1	1	1	-	High	Low
LVCMOS 1.5 V	1	1	1	~	1	-	_	High	Low

Table 8-15 • IGLOOe and ProASIC3E I/O Standards—Output Drive and Slew Rate

# 9 – I/O Software Control in Low Power Flash Devices

Fusion, IGLOO, and ProASIC3 I/Os provide more design flexibility, allowing the user to control specific features by enabling certain I/O standards. Some features are selectable only for certain I/O standards, whereas others are available for all I/O standards. For example, slew control is not supported by differential I/O standards. Conversely, I/O register combining is supported by all I/O standards. For detailed information about which I/O standards and features are available on each device and each I/O type, refer to the I/O Structures section of the handbook for the device you are using.

Figure 9-1 shows the various points in the software design flow where a user can provide input or control of the I/O selection and parameters. A detailed description is provided throughout this document.



Figure 9-1 • User I/O Assignment Flow Chart

# 10 – DDR for Microsemi's Low Power Flash Devices

## Introduction

The I/Os in Fusion, IGLOO, and ProASIC3 devices support Double Data Rate (DDR) mode. In this mode, new data is present on every transition (or clock edge) of the clock signal. This mode doubles the data transfer rate compared with Single Data Rate (SDR) mode, where new data is present on one transition (or clock edge) of the clock signal. Low power flash devices have DDR circuitry built into the I/O tiles. I/Os are configured to be DDR receivers or transmitters by instantiating the appropriate special macros (examples shown in Figure 10-4 on page 276 and Figure 10-5 on page 277) and buffers (DDR\_OUT or DDR\_REG) in the RTL design. This document discusses the options the user can choose to configure the I/Os in this mode and how to instantiate them in the design.

# Double Data Rate (DDR) Architecture

Low power flash devices support 350 MHz DDR inputs and outputs. In DDR mode, new data is present on every transition of the clock signal. Clock and data lines have identical bandwidths and signal integrity requirements, making them very efficient for implementing very high-speed systems. High-speed DDR interfaces can be implemented using LVDS (not applicable for IGLOO nano and ProASIC3 nano devices). In IGLOOe, ProASIC3E, AFS600, and AFS1500 devices, DDR interfaces can also be implemented using the HSTL, SSTL, and LVPECL I/O standards. The DDR feature is primarily implemented in the FPGA core periphery and is not tied to a specific I/O technology or limited to any I/O standard.



Figure 10-1 • DDR Support in Low Power Flash Devices

In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X

- 3. A single STAPL file or multiple STAPL files with multiple FlashROM contents. A single STAPL file will be generated if the device serialization feature is not used. You can program the whole FlashROM or selectively program individual pages.
- 4. A single STAPL file to configure the security settings for the device, such as the AES Key and/or Pass Key.



Figure 13-4 • Flexible Programming File Generation for Different Applications

## **Programming Solution**

For device programming, any IEEE 1532–compliant programmer can be used; however, the FlashPro4/3/3X programmer must be used to control the low power flash device's rich security features and FlashROM programming options. The FlashPro4/3/3X programmer is a low-cost portable programmer for the Microsemi flash families. It can also be used with a powered USB hub for parallel programming. General specifications for the FlashPro4/3/3X programmer are as follows:

- Programming clock TCK is used with a maximum frequency of 20 MHz, and the default frequency is 4 MHz.
- Programming file STAPL
- Daisy chain Supported. You can use the ChainBuilder software to build the programming file for the chain.
- Parallel programming Supported. Multiple FlashPro4/3/3X programmers can be connected together using a powered USB hub or through the multiple USB ports on the PC.
- Power supply The target board must provide VCC, VCCI, VPUMP, and VJTAG during programming. However, if there is only one device on the target board, the FlashPro4/3/3X programmer can generate the required VPUMP voltage from the USB port.

# **Programming Algorithm**

## **JTAG Interface**

The low power flash families are fully compliant with the IEEE 1149.1 (JTAG) standard. They support all the mandatory boundary scan instructions (EXTEST, SAMPLE/PRELOAD, and BYPASS) as well as six optional public instructions (USERCODE, IDCODE, HIGHZ, and CLAMP).

#### **IEEE 1532**

The low power flash families are also fully compliant with the IEEE 1532 programming standard. The IEEE 1532 standard adds programming instructions and associated data registers to devices that comply with the IEEE 1149.1 standard (JTAG). These instructions and registers extend the capabilities of the IEEE 1149.1 standard such that the Test Access Port (TAP) can be used for configuration activities. The IEEE 1532 standard greatly simplifies the programming algorithm, reducing the amount of time needed to implement microprocessor ISP.

## **Implementation Overview**

To implement device programming with a microprocessor, the user should first download the C-based STAPL player or DirectC code from the Microsemi SoC Products Group website. Refer to the website for future updates regarding the STAPL player and DirectC code.

http://www.microsemi.com/soc/download/program\_debug/stapl/default.aspx

http://www.microsemi.com/soc/download/program\_debug/directc/default.aspx

Using the easy-to-follow user's guide, create the low-level application programming interface (API) to provide the necessary basic functions. These API functions act as the interface between the programming software and the actual hardware (Figure 15-2).



#### Figure 15-2 • Device Programming Code Relationship

The API is then linked with the STAPL player or DirectC and compiled using the microprocessor's compiler. Once the entire code is compiled, the user must download the resulting binary into the MCU system's program memory (such as ROM, EEPROM, or flash). The system is now ready for programming.

To program a design into the FPGA, the user creates a bitstream or STAPL file using the Microsemi Designer software, downloads it into the MCU system's volatile memory, and activates the stored programming binary file (Figure 15-3 on page 352). Once the programming is completed, the bitstream or STAPL file can be removed from the system, as the configuration profile is stored in the flash FPGA fabric and does not need to be reloaded at every system power-on.



Note: TCK is correctly wired with an equivalent tie-off resistance of  $500 \Omega$ , which satisfies the table for VJTAG of 1.5 V. The resistor values for TRST are not appropriate in this case, as the tie-off resistance of  $375 \Omega$  is below the recommended minimum for VJTAG = 1.5 V, but would be appropriate for a VJTAG setting of 2.5 V or 3.3 V.

#### Figure 16-3 • Parallel Resistance on JTAG Chain of Devices

## **Advanced Boundary Scan Register Settings**

You will not be able to control the order in which I/Os are released from boundary scan control. Testing has produced cases where, depending on I/O placement and FPGA routing, a 5 ns glitch has been seen on exiting programming mode. The following setting is recommended to prevent such I/O glitches:

- 1. In the FlashPro software, configure the advanced BSR settings for **Specify I/O Settings During Programming**.
- 2. Set the input BSR cell to **Low** for the input I/O.